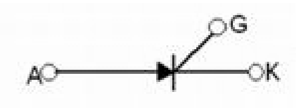
MCR100-6U-8U Plastic-Encapsulate Thyristors

Silicon Controlled Rectifier



FEATURES

Current-I_{GT} : 200 μA

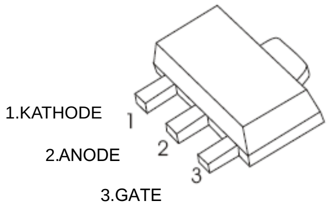
I_{TRMS} : 0.8 A

V_{RRM}/ V_{DRM} : MCR100-6: 400 V

MCR100-8: 600 V

Operating and storage junction temperature range

T_J，T_{stg} : -55℃ to +150℃



SOT-89-3L

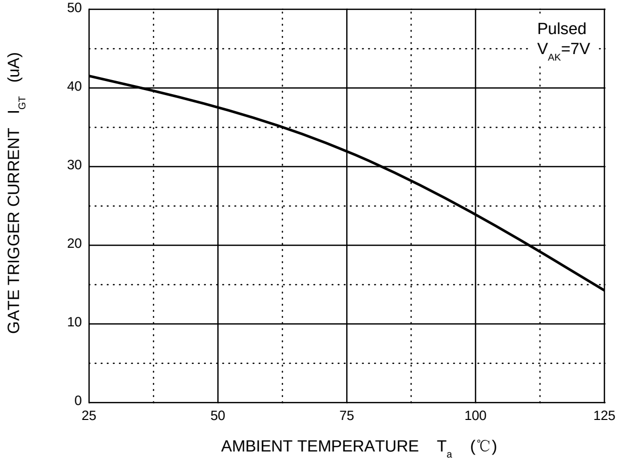
ELECTRICAL CHARACTERISTICS（Ta=25℃ unless otherwise specified）

Parameter	Symbol		Test conditions	Min	Max	Unit
On state voltage	V_{TM}*		I_{TM}=1A		1.7	V
Gate trigger voltage	V_{GT}		V_{AK}=7V		0.8	V
Peak Repetitive forward and reverse blocking voltage **MCR100-6** **MCR100-8**	V_{DRM} AND V_{RRM}		I_{DRM}= 10 μA	400 600		V
Peak forward or reverse blocking Current	I_{DRM} I_{RRM}		V_{AK}= Rated V_{DRM} or V_{RRM}		10	μA
Holding current	I_H		I_{HL}= 20mA ,V_{AK} = 7V		5	mA
Gate trigger current	I_{GT}	A2	V_{AK}=7V	5	15	μA
		A1		15	30	μA
		A		30	80	μA
		B		80	200	μA

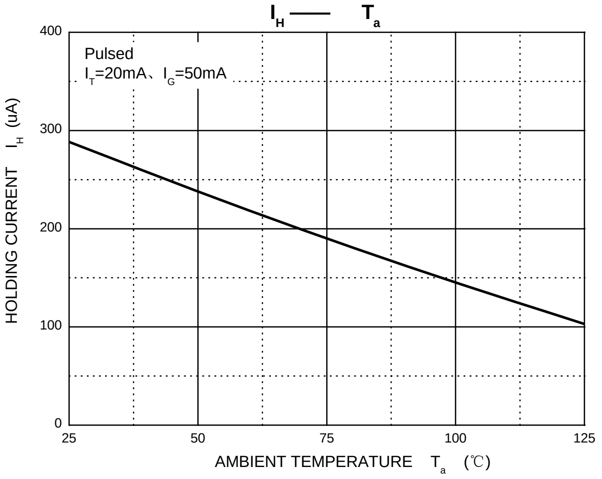
* Forward current applied for 1 ms maximum duration，duty cycle≤1%。

Typical Characteristics

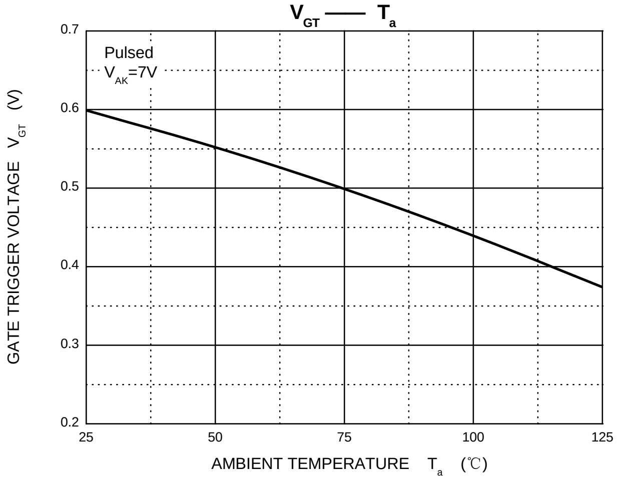
I_{GT} —— T_a



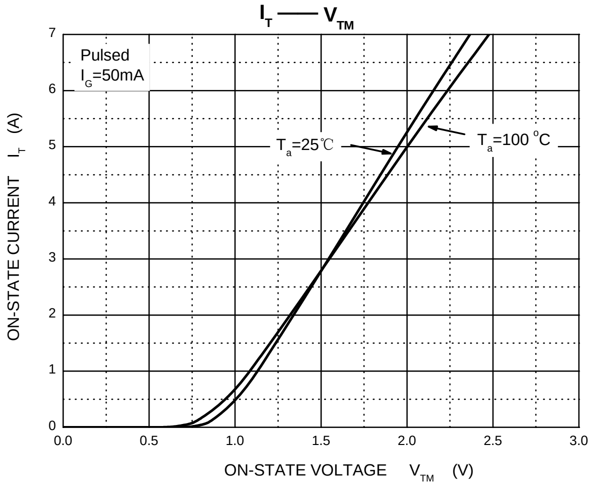
I_H —— T_a



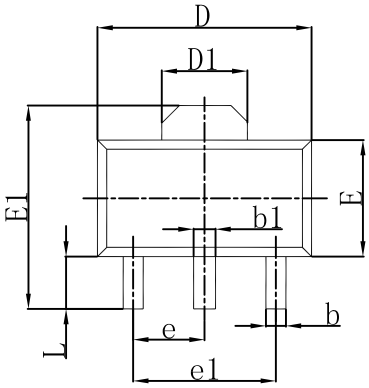
V_{GT} —— T_a

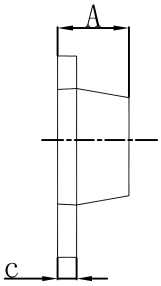


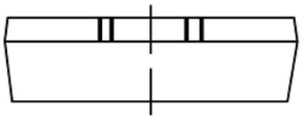
I_T —— V_{TM}



SOT-89-3L Outlines Dimensions







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047